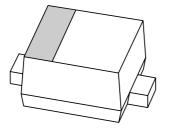
# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# **PMEG2005EB**Low V<sub>F</sub> MEGA Schottky barrier diode

Product data sheet Supersedes data of 2003 Feb 20 2003 Apr 04



# Low V<sub>F</sub> MEGA Schottky barrier diode

# PMEG2005EB

### **FEATURES**

Forward current: 0.5 AReverse voltage: 20 V

Very low forward voltage

· Guard ring protected

• Ultra small SMD package.

### **APPLICATIONS**

• Ultra high-speed switching

· Voltage clamping

· Protection circuits

· Low current rectification

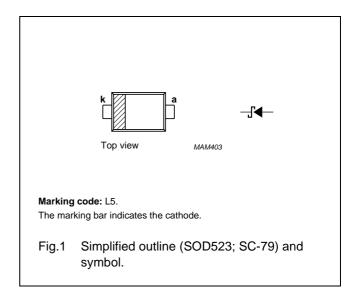
Low power consumption applications (e.g. handheld devices).

### **DESCRIPTION**

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode, encapsulated in a SOD523 (SC-79) ultra small SMD plastic package.

### **PINNING**

PIN	DESCRIPTION	
1	cathode	
2	anode	



### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_R$	continuous reverse voltage		_	20	V
I <sub>F</sub>	continuous forward current		_	500	mA
I <sub>FRM</sub>	repetitive peak forward current	$t_p$ = 1 ms; $\delta \le 0.25$	_	3.5	Α
I <sub>FSM</sub>	non-repetitive peak forward current	t = 8 ms square wave	_	6	Α
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T <sub>amb</sub>	operating ambient temperature		-65	+125	°C

# Low V<sub>F</sub> MEGA Schottky barrier diode

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# **ELECTRICAL CHARACTERISTICS**

 $T_{amb}$  = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V <sub>F</sub>	continuous forward voltage	see Fig.2			
		I <sub>F</sub> = 0.1 mA	120	180	mV
		I <sub>F</sub> = 1 mA	180	240	mV
		I <sub>F</sub> = 10 mA	245	290	mV
		I <sub>F</sub> = 100 mA	320	380	mV
		I <sub>F</sub> = 500 mA	430	480	mV
I <sub>R</sub>	continuous reverse current	V <sub>R</sub> = 10 V; see Fig.3; note 1	7	30	μΑ
C <sub>d</sub>	diode capacitance	$V_R = 1 V$ ; $f = 1 MHz$ ; see Fig.4	24	30	pF

# Note

1. Pulsed test:  $t_p$  = 300  $\mu$ s;  $\delta$  = 0.02.

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to	note 1	400	K/W
	ambient			

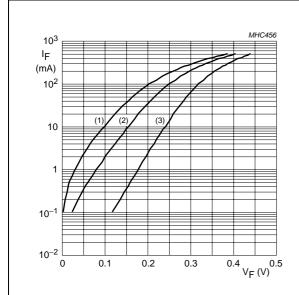
# Note

1. Refer to SOD523 (SC-79) standard mounting conditions.

# Low V<sub>F</sub> MEGA Schottky barrier diode

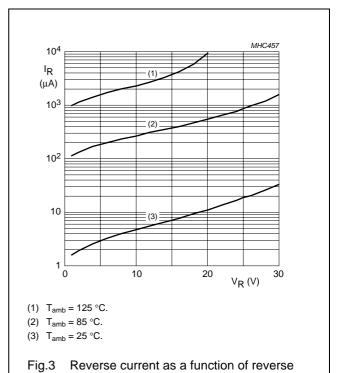
# PMEG2005EB

# **GRAPHICAL DATA**



- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.2 Forward current as a function of forward voltage; typical values.



voltage; typical values.

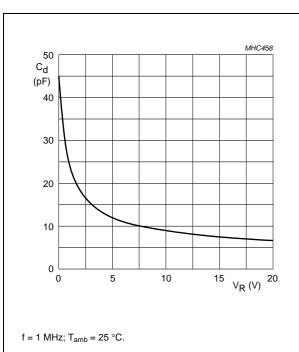


Fig.4 Diode capacitance as a function of reverse voltage; typical values.

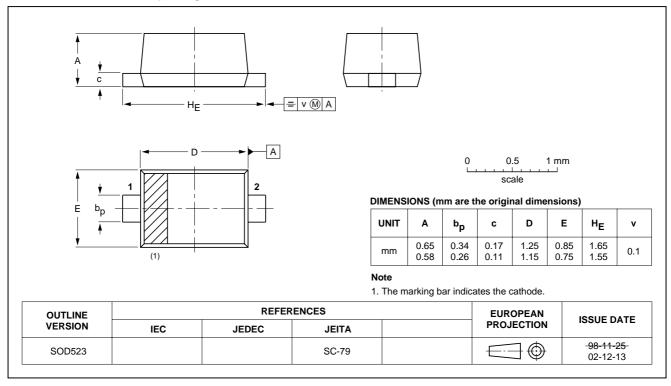
# Low V<sub>F</sub> MEGA Schottky barrier diode

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# **PACKAGE OUTLINE**

# Plastic surface mounted package; 2 leads

**SOD523** 



# Low V<sub>F</sub> MEGA Schottky barrier diode

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### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
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